Supplemental material for

Ultrafast nonlinear optical absorption and carrier dynamics of CrPS₄ thin films

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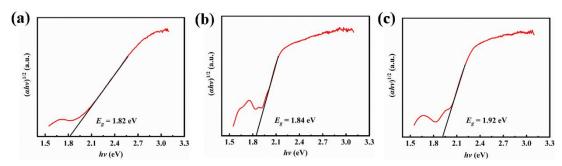


Fig. S1. The bandgap of CrPS₄ with different thicknesses. (a) 105nm, (b) 510 nm, and (c) 1086 nm.

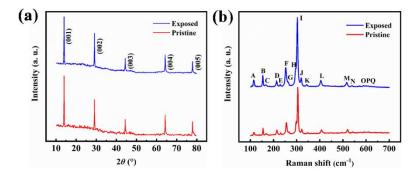


FIG. S2. The comparison of (a) XRD pattern and (b) Raman spectra of CrPS₄ before and after air exposure.

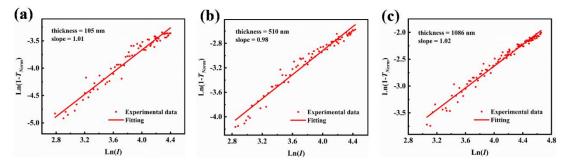


Fig. S3. Plots of $ln(1-T_{Norm})$ versus ln(I) of (a) 105 nm, (b) 510 nm, and (c) 1086 nm CrPS₄.

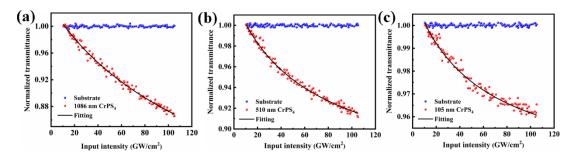


FIG. S4. Nonlinear absorption results of CrPS₄ and sapphire substrate.

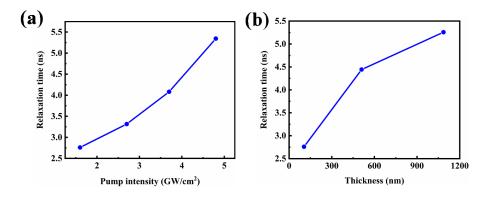


Fig. S5. Relaxation time τ_3 with different (a) pump intensity and (b) thickness of CrPS₄.

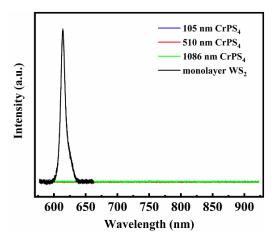


Fig. S6. Photoluminescence spectra of monolayer WS2 and CrPS4 at different thicknesses.

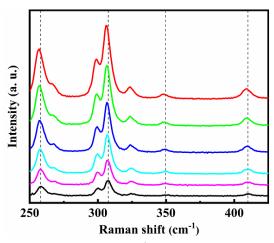


Fig. S7. Raman spectra from 250 to 425 cm⁻¹ excited at 532 nm under different powers corresponding to Fig. 5(b).